

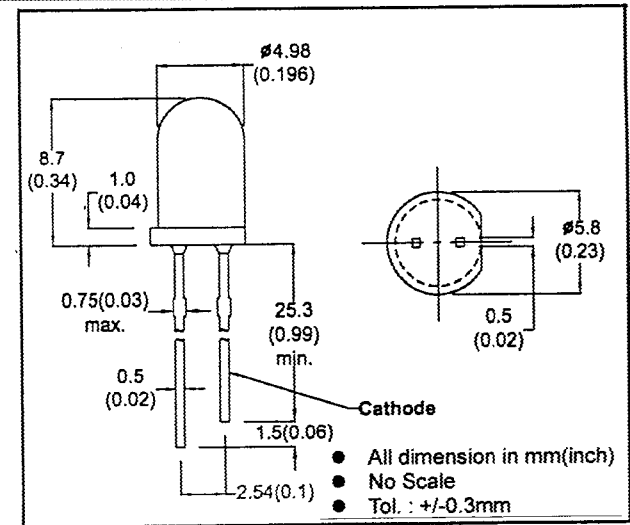
DESCRIPTION

MIB57TA-J and MIB57TA-K are GaAlAs infrared emitting diode molded in a 5mm diameter clear transparent lens.

ABSOLUTE MAXIMUM RATINGS

Forward Current (Continuous)	100mA
Pulse Forward Current	1A*
Reverse Voltage (Continuous)	6V
Power Dissipation	175mW
Operating Temperature Range	-40 to +100°C
Lead Soldering Temperature (1/16" from body)	260°C for 5 sec.

* Pulse Width = 10μs, Duty Ratio = 0.01.



ELECTRO-OPTICAL CHARACTERISTICS (Ta=25°C)

PARAMETER	SYMBOL	MIN	TYP	MAX	UNIT	CONDITIONS
Radiant Power Output	Po	7.5	10		mW	IF=20mA
		5.5	8		mW	IF=20mA
Forward Voltage	VF		1.65	2	V	IF=10mA
			1.65	2	V	IF=10mA
Reverse Current	IR			100	μA	VR=4V
				100	μA	VR=4V
Peak Wavelength	λp		880		nm	IF=20mA
			880		nm	IF=20mA
Spectrum Line Half Width	Δλ		80		nm	IF=20mA
			80		nm	IF=20mA
Viewing Angle	2θ 1/2		30		degree	IF=20mA
			70		degree	IF=20mA



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